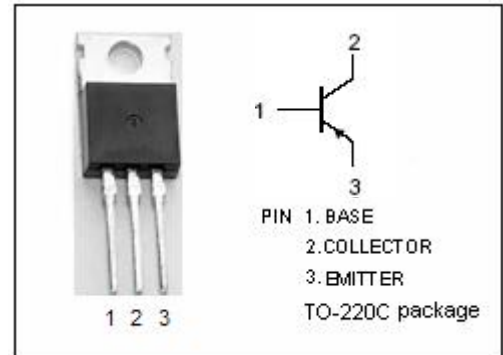


**isc Silicon PNP Power Transistor**
**KTA1276**
**DESCRIPTION**

- Collector-Emitter Breakdown Voltage  
:  $V_{(BR)CEO} = -30V(\text{Min})$
- Good Linearity of  $h_{FE}$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

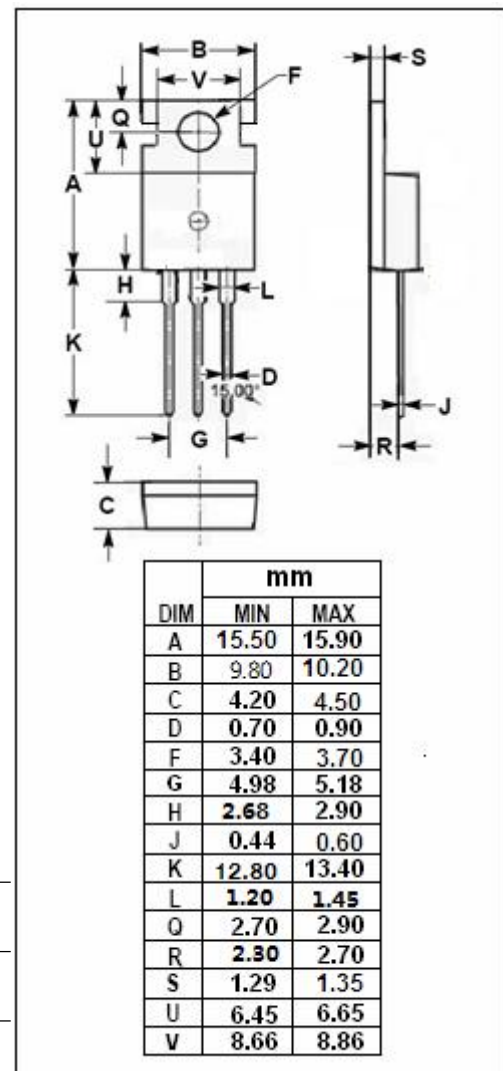
- Designed for general purpose applications.


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-30	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-3	A
$P_C$	Total Power Dissipation @ $T_C=25^\circ\text{C}$	20	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	63	$^\circ\text{C/W}$



## isc Silicon PNP Power Transistor

KTA1276

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-30			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA ; I <sub>B</sub> = 0	-30			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			-0.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V			-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -20V; I <sub>E</sub> = 0			-1.0	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1.0	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V	70		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -2.5A; V <sub>CE</sub> = -2V	25			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V		100		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1.0MHz		40		pF

◆ h<sub>FE-1</sub> Classifications

O	Y
70-140	120-240

**Notice:**

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